

Fig.1.

Growth of multiple non-compositional-graded layers

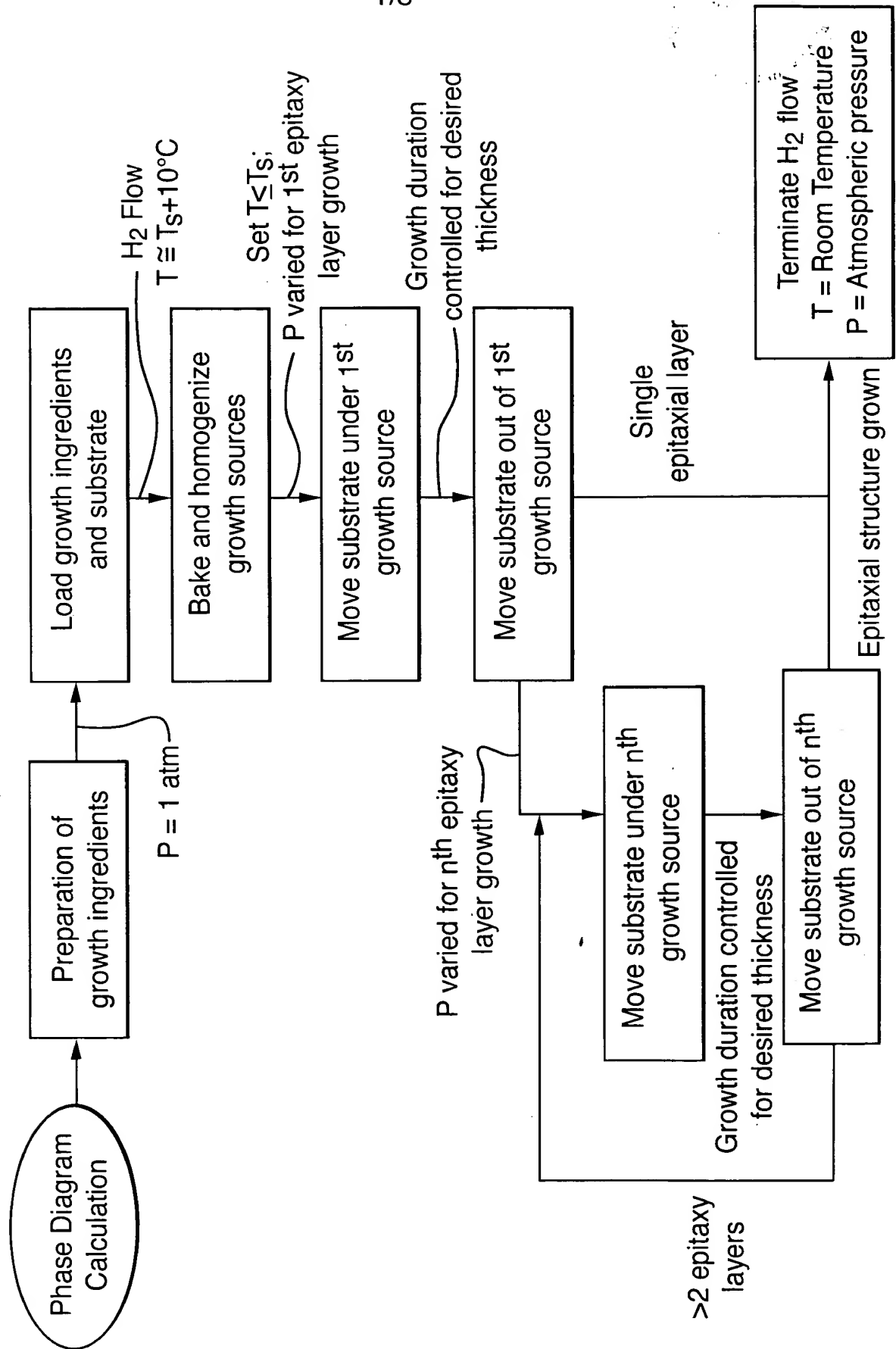


Fig.2.

Growth of compositional-graded layer

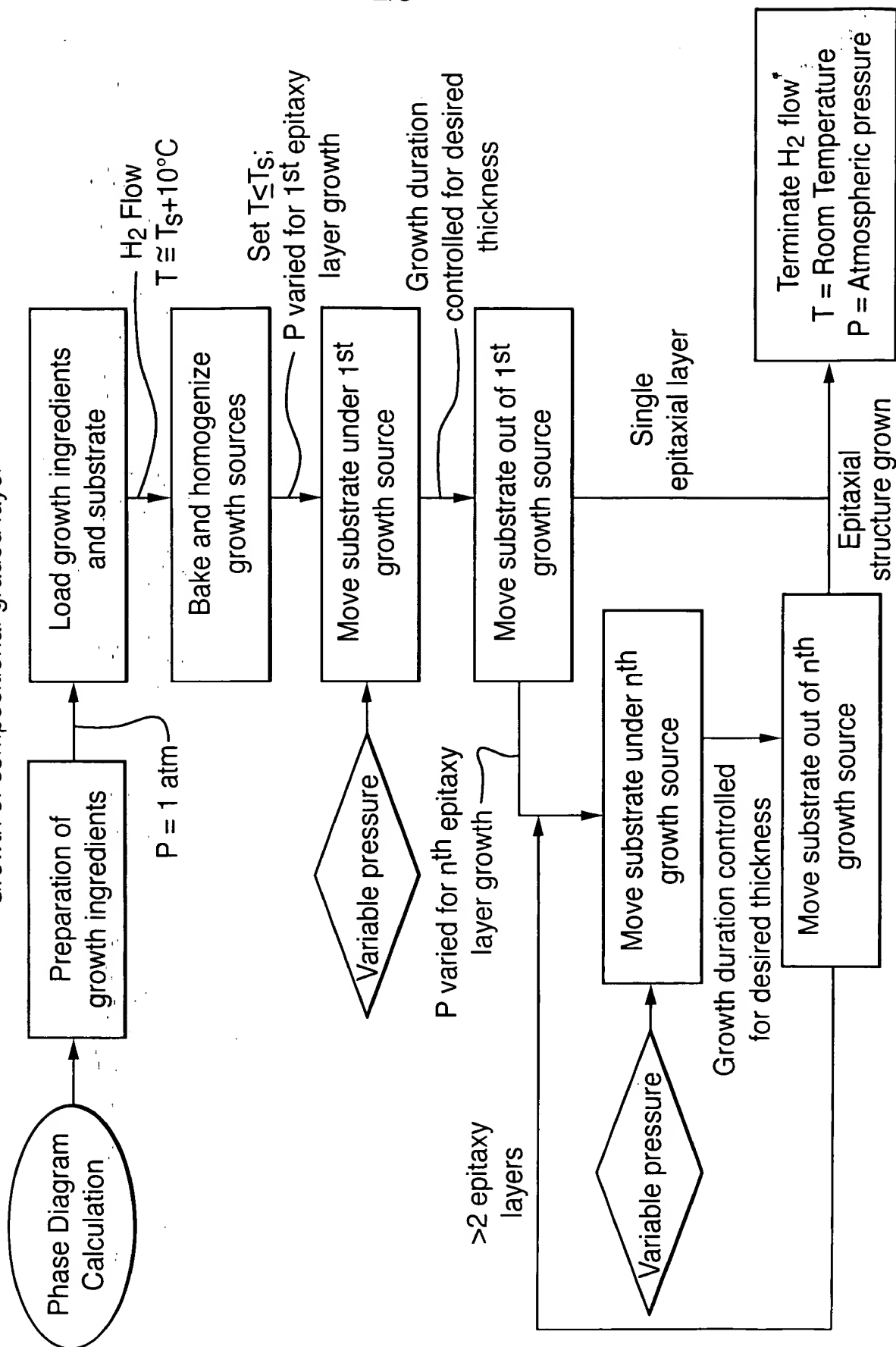


Fig.3.

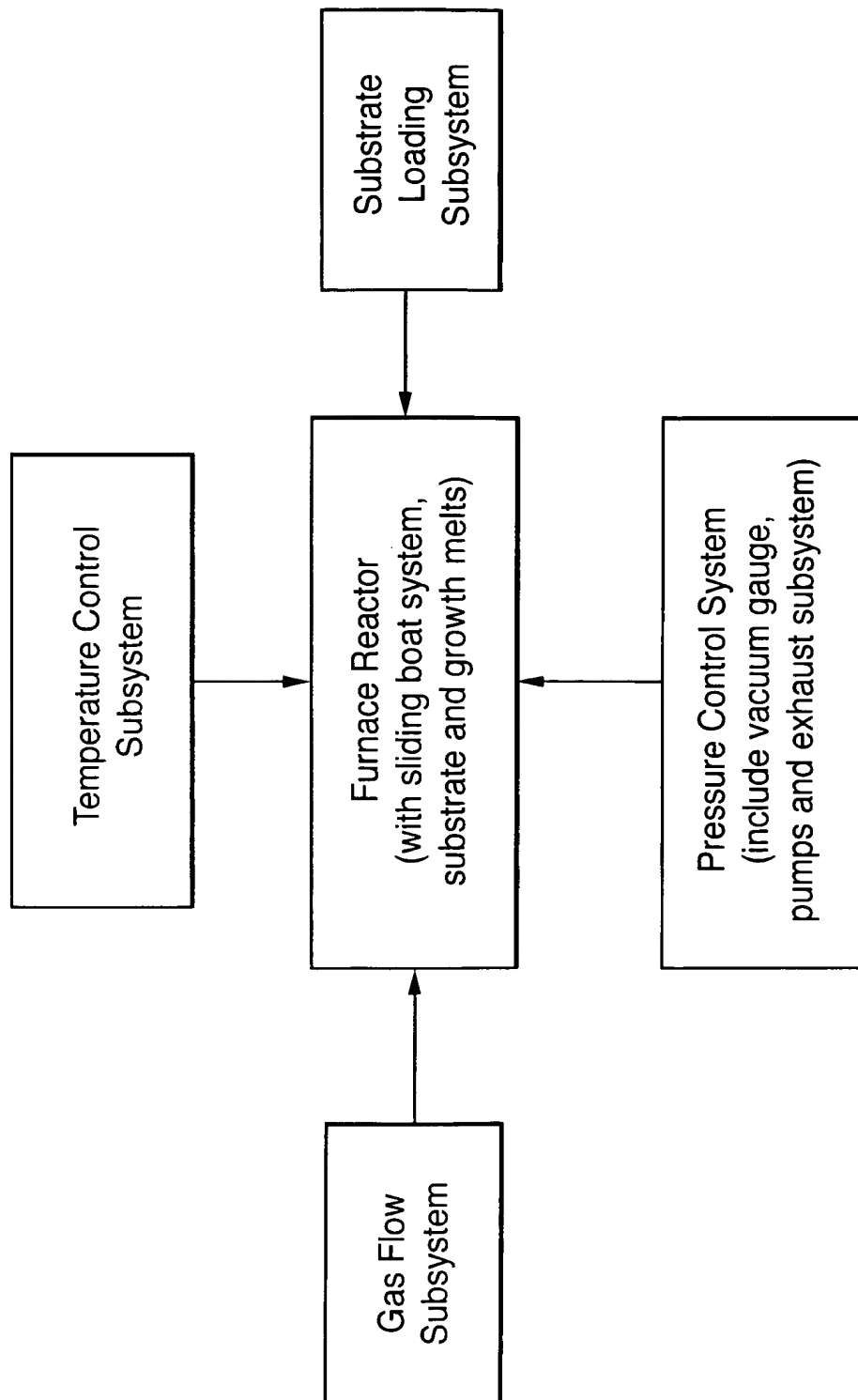
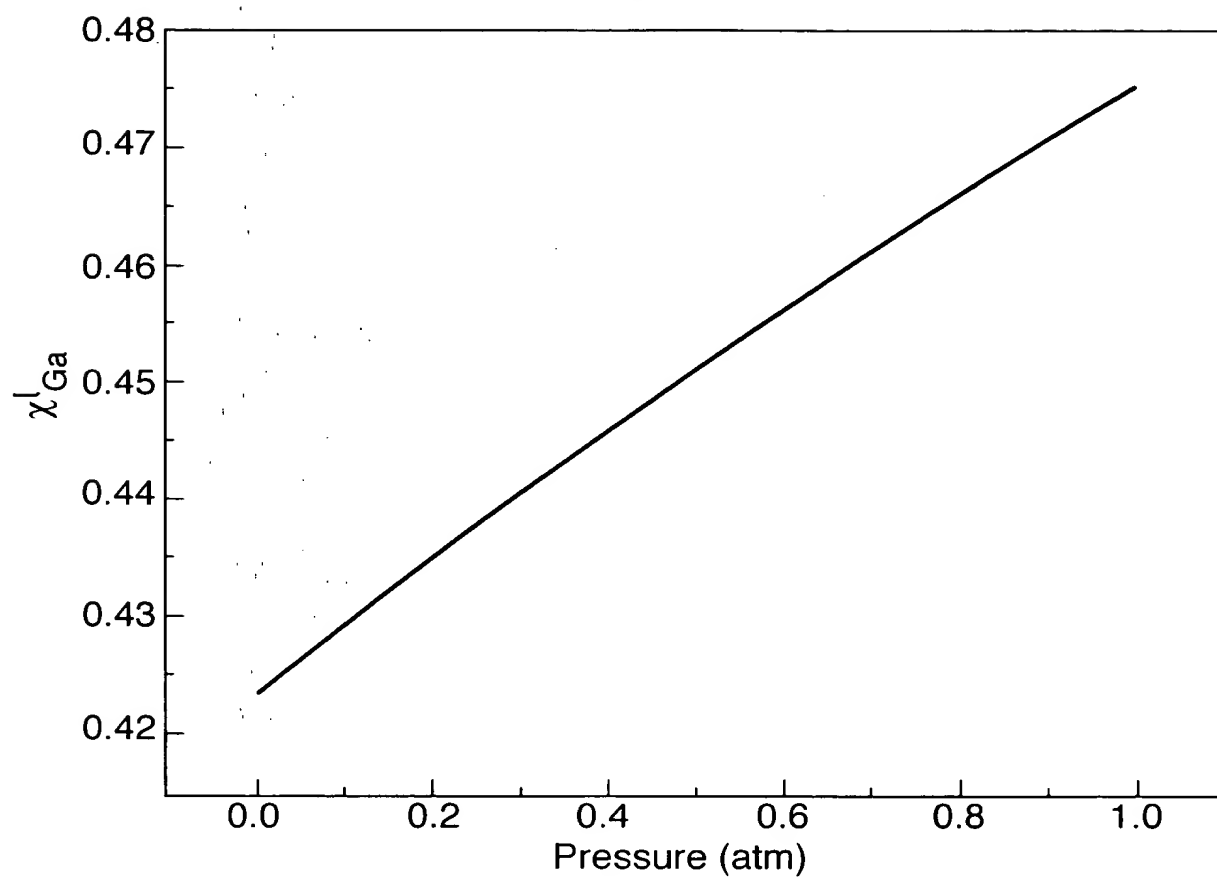
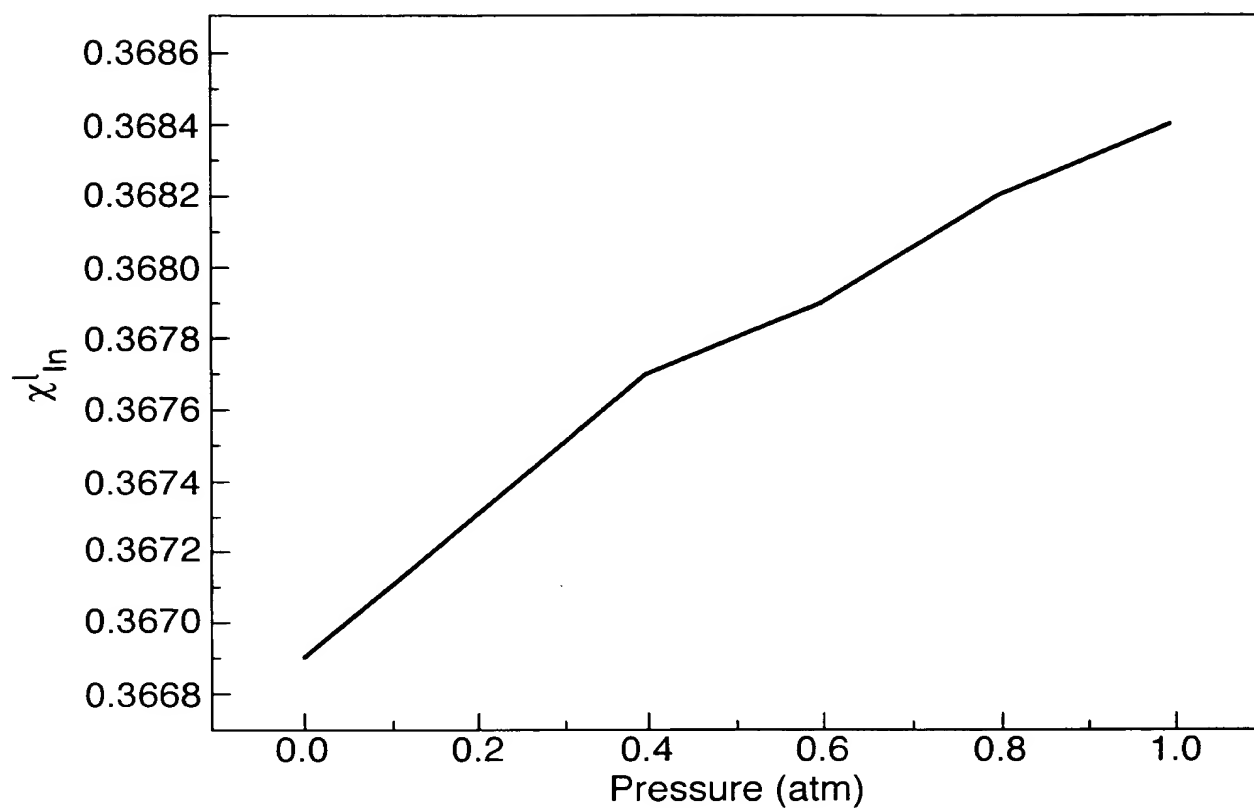


Fig.4.



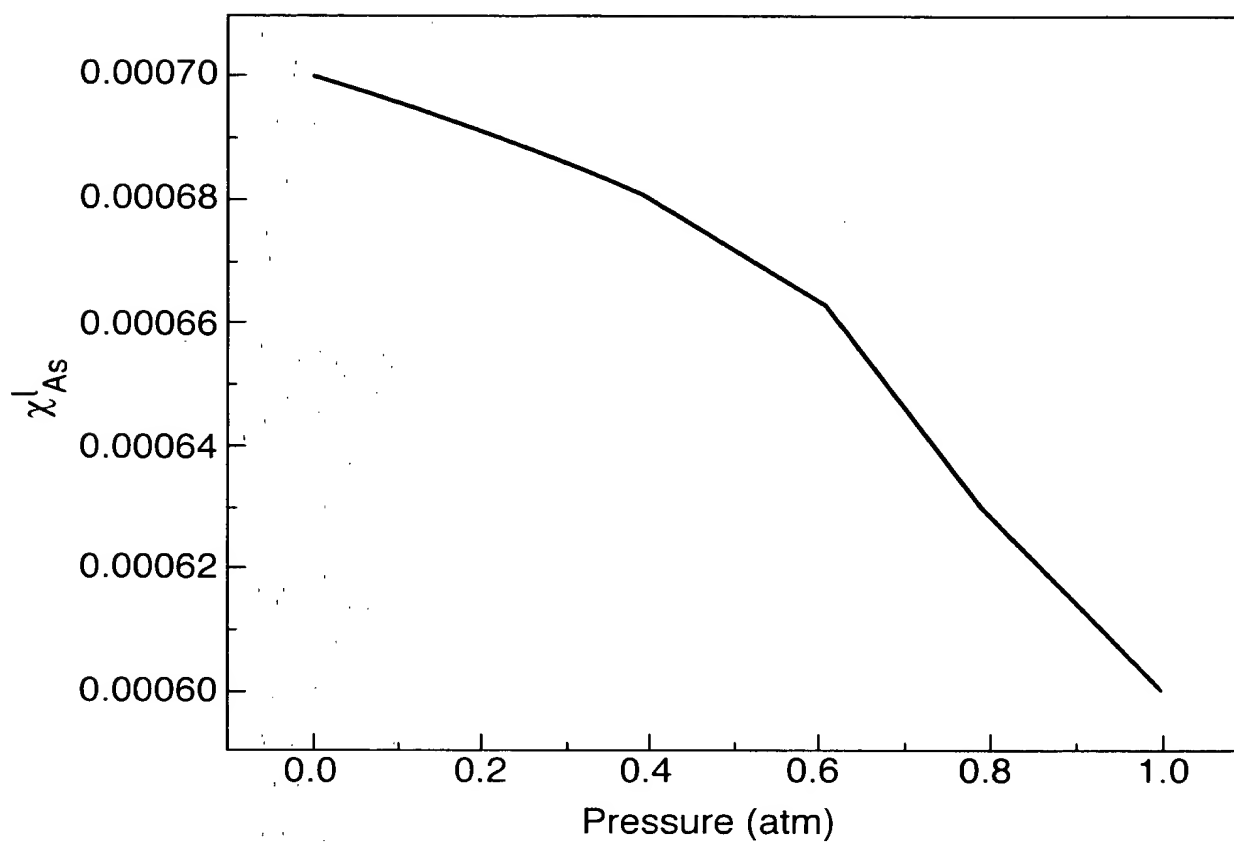
Atomic fraction  $x_{\text{Ga}}^{\text{l}}$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.5.



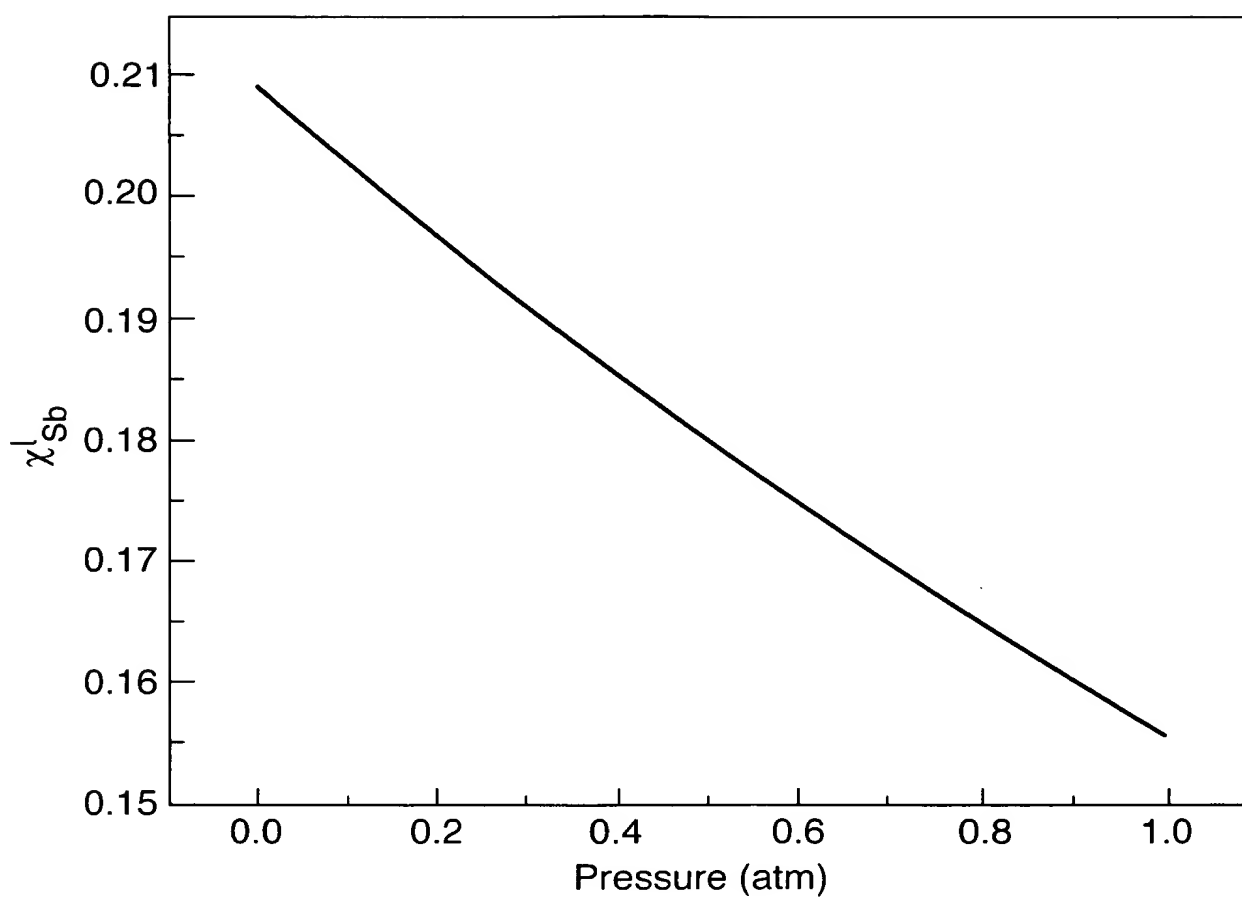
Atomic fraction  $\chi_{\text{In}}^l$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.6.



Atomic fraction  $\chi^l_{As}$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.7.



Atomic fraction  $\chi_{\text{Sb}}^l$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.8(a).

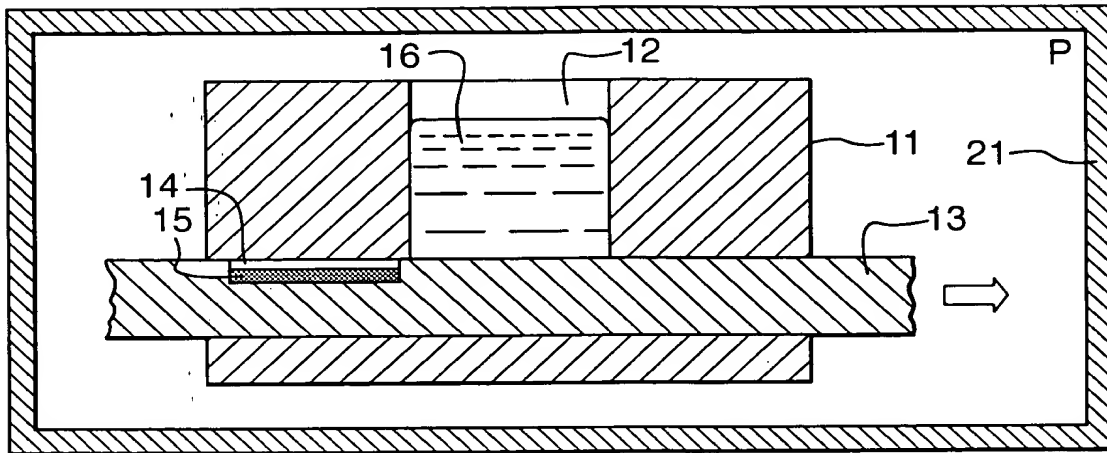


Fig.8(b).

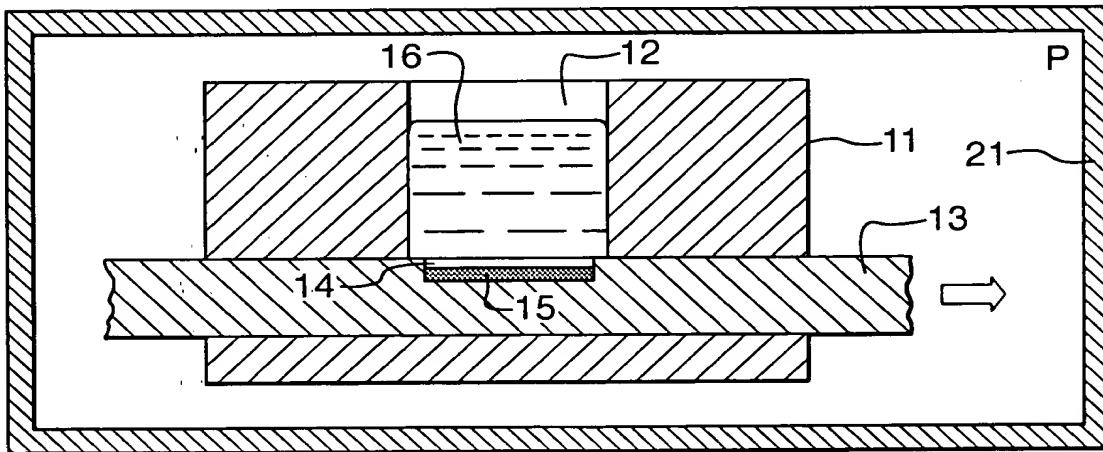
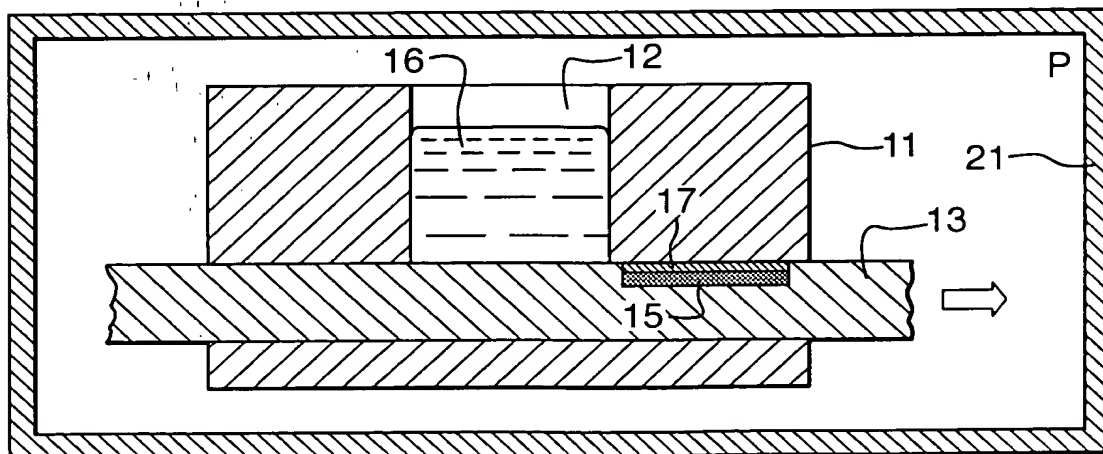


Fig.8(c).





#3

**FIGURE 1**

# Growth of multiple non-compositional-graded layers

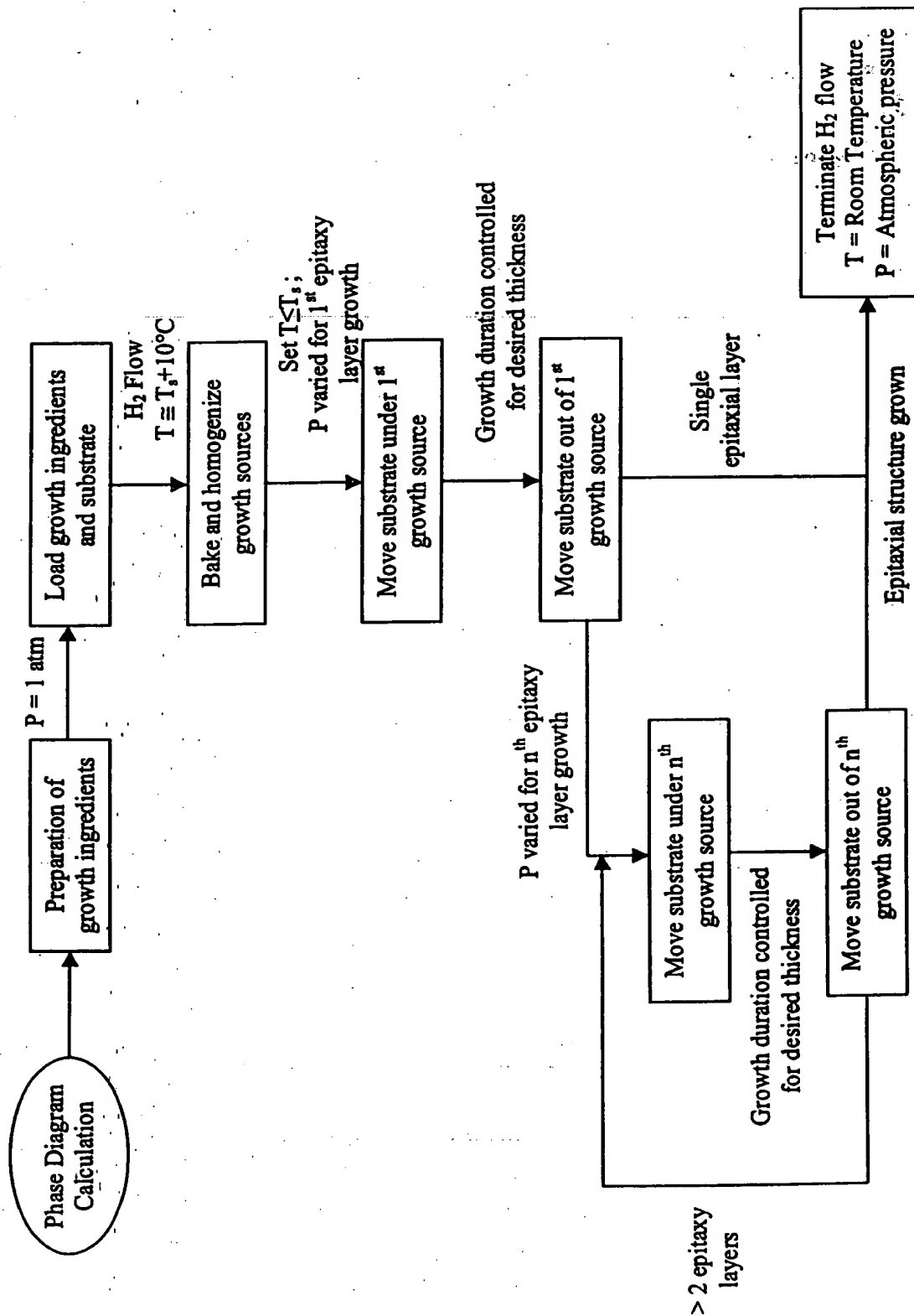


FIGURE 2

## Growth of compositional-graded layer

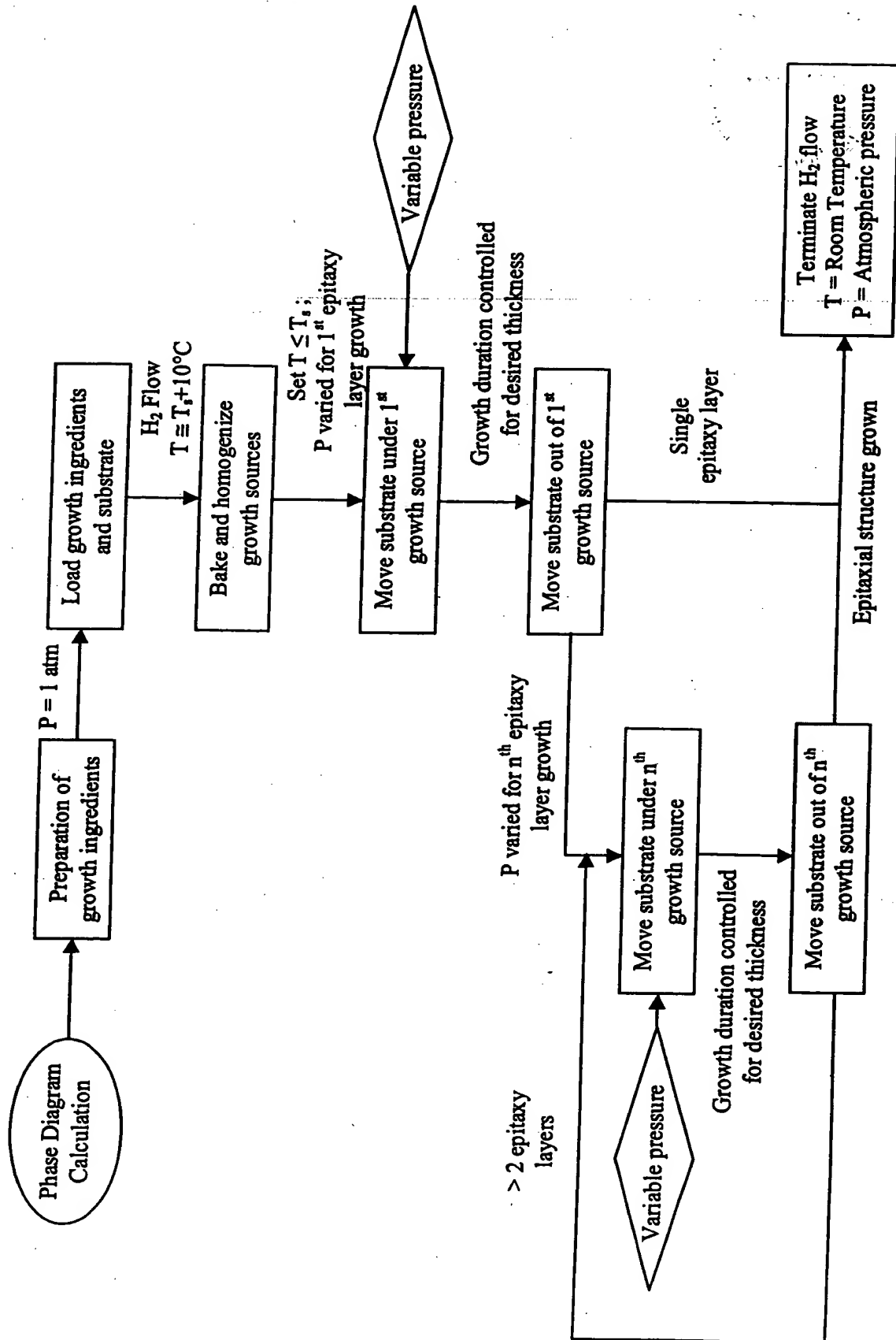


FIGURE 3

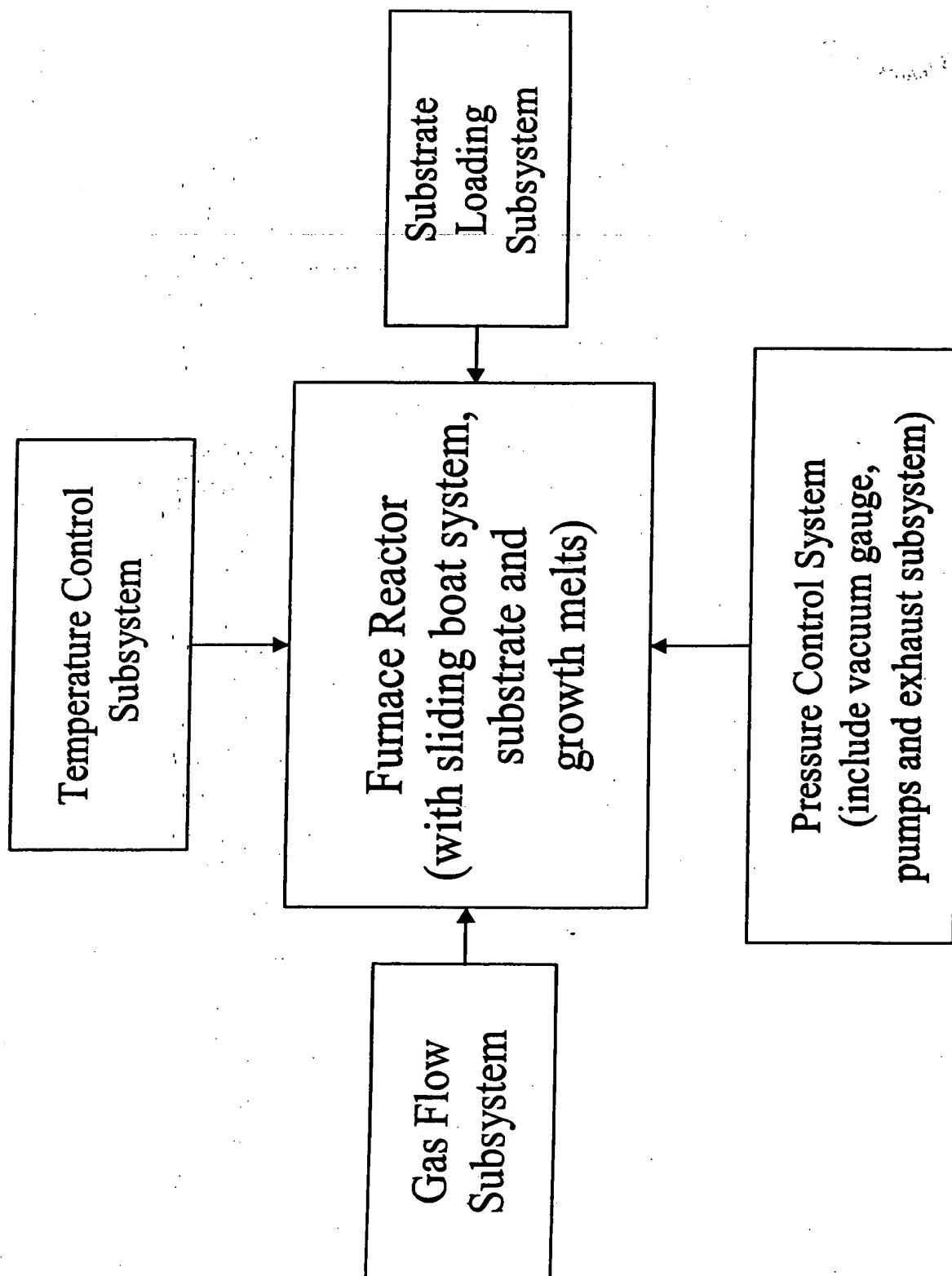
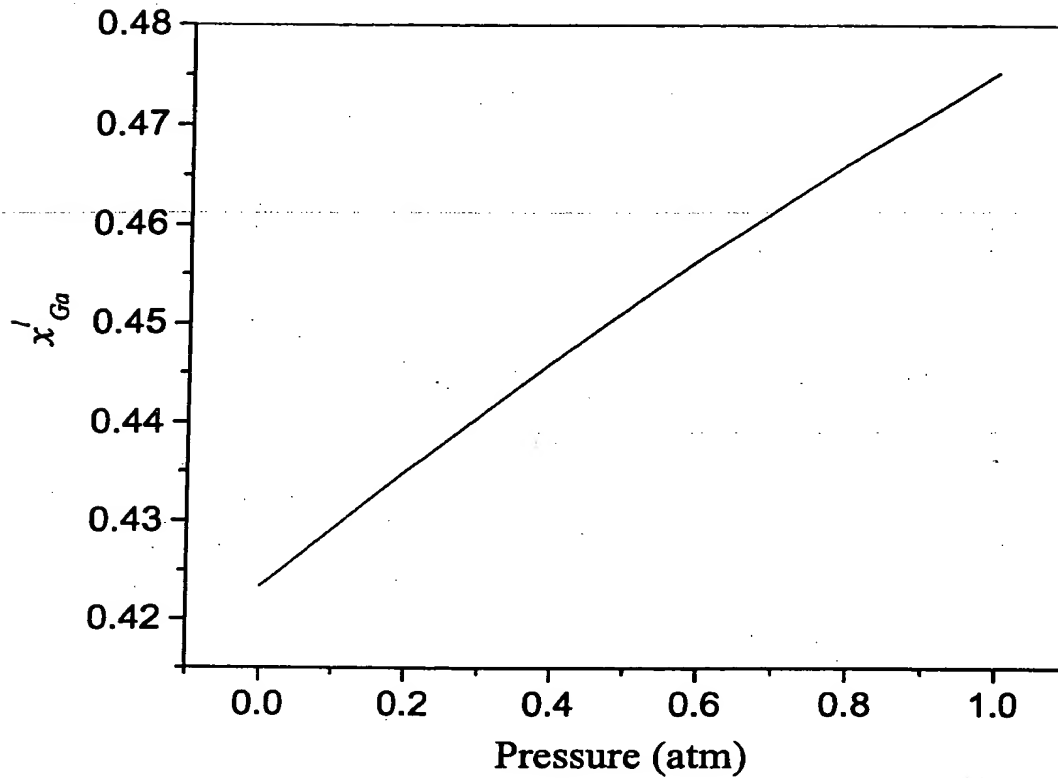
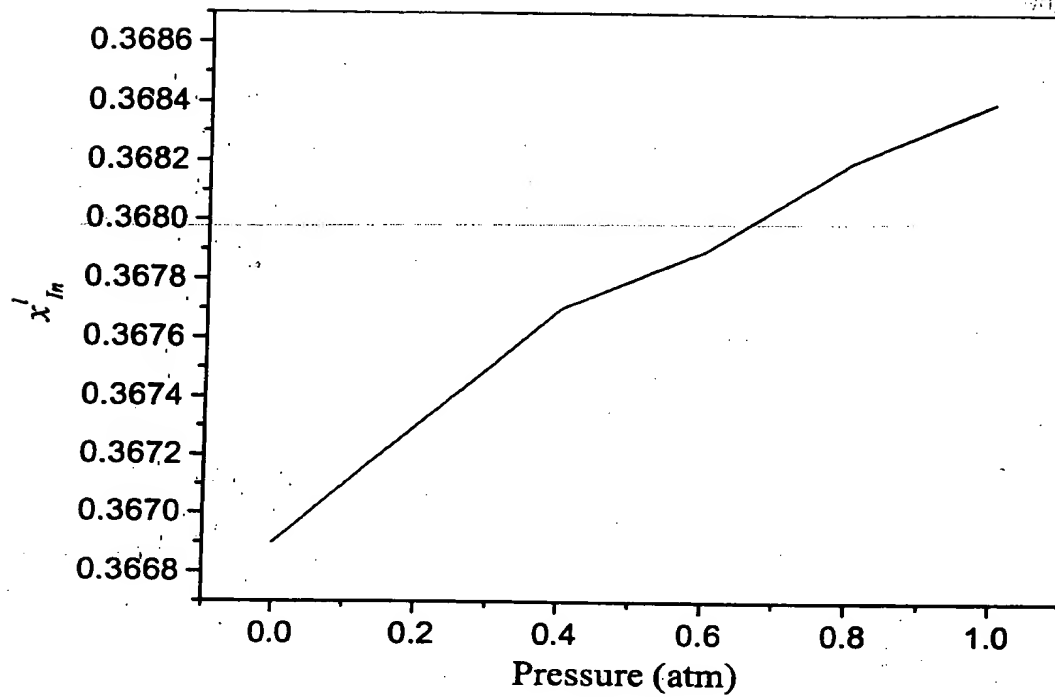
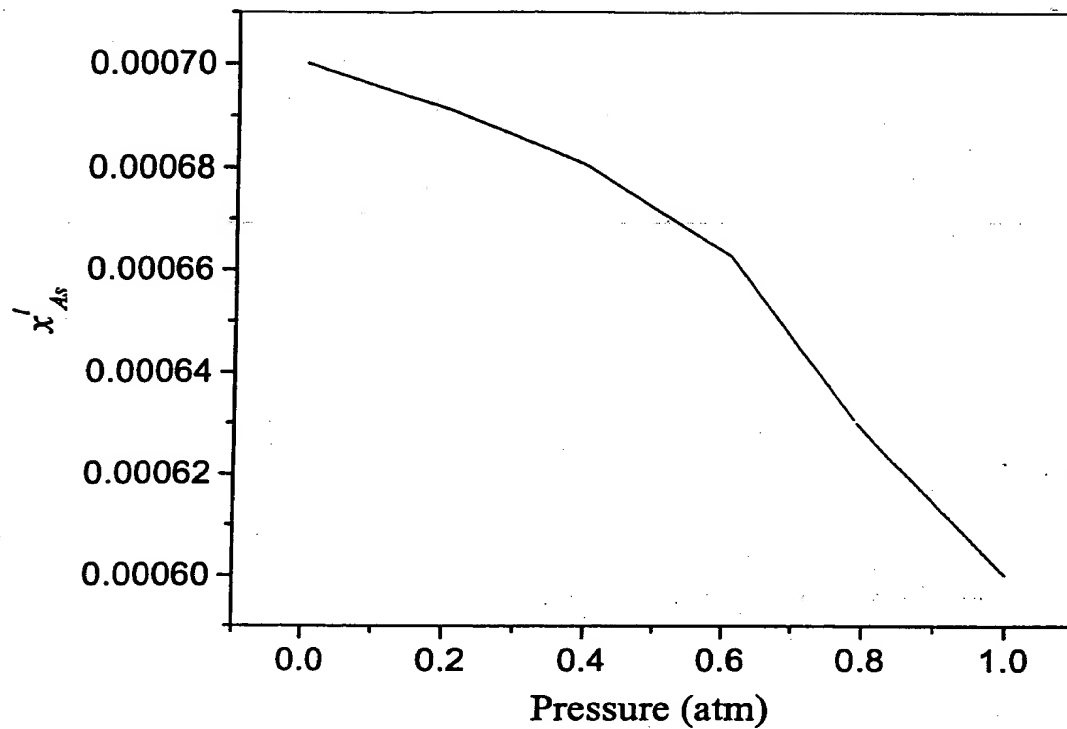


FIGURE 4

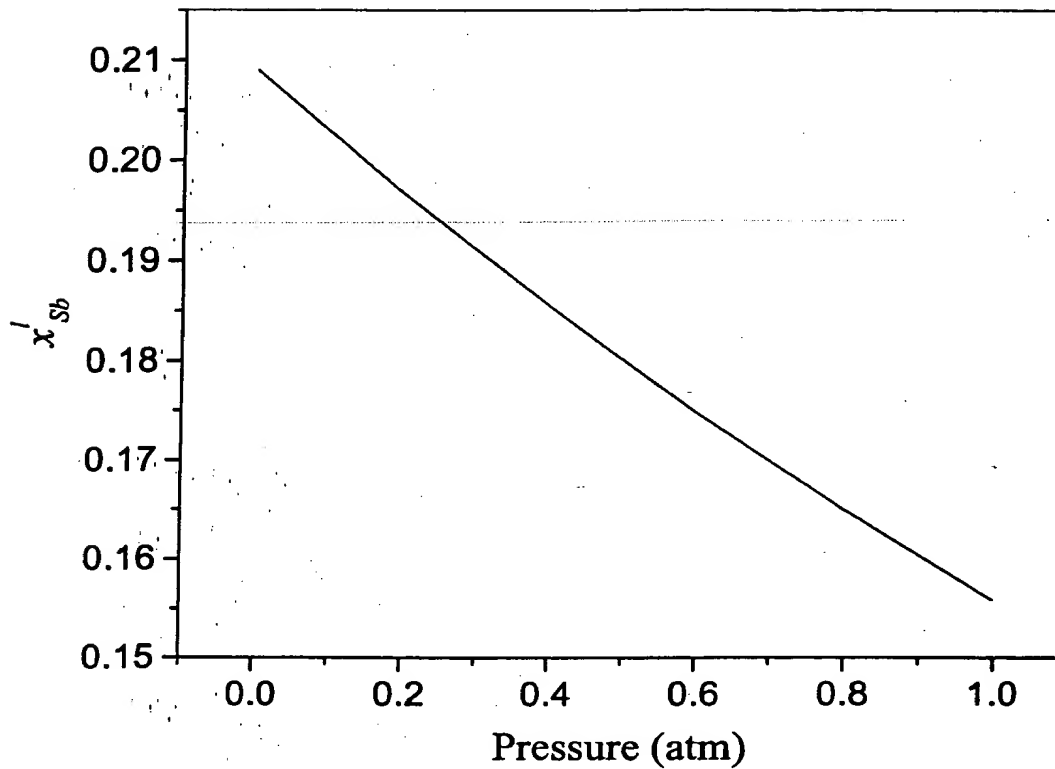
Atomic fraction  $x'_{Ga}$  in melt for  $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 5

Atomic fraction  $x'_{In}$  in melt for  $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

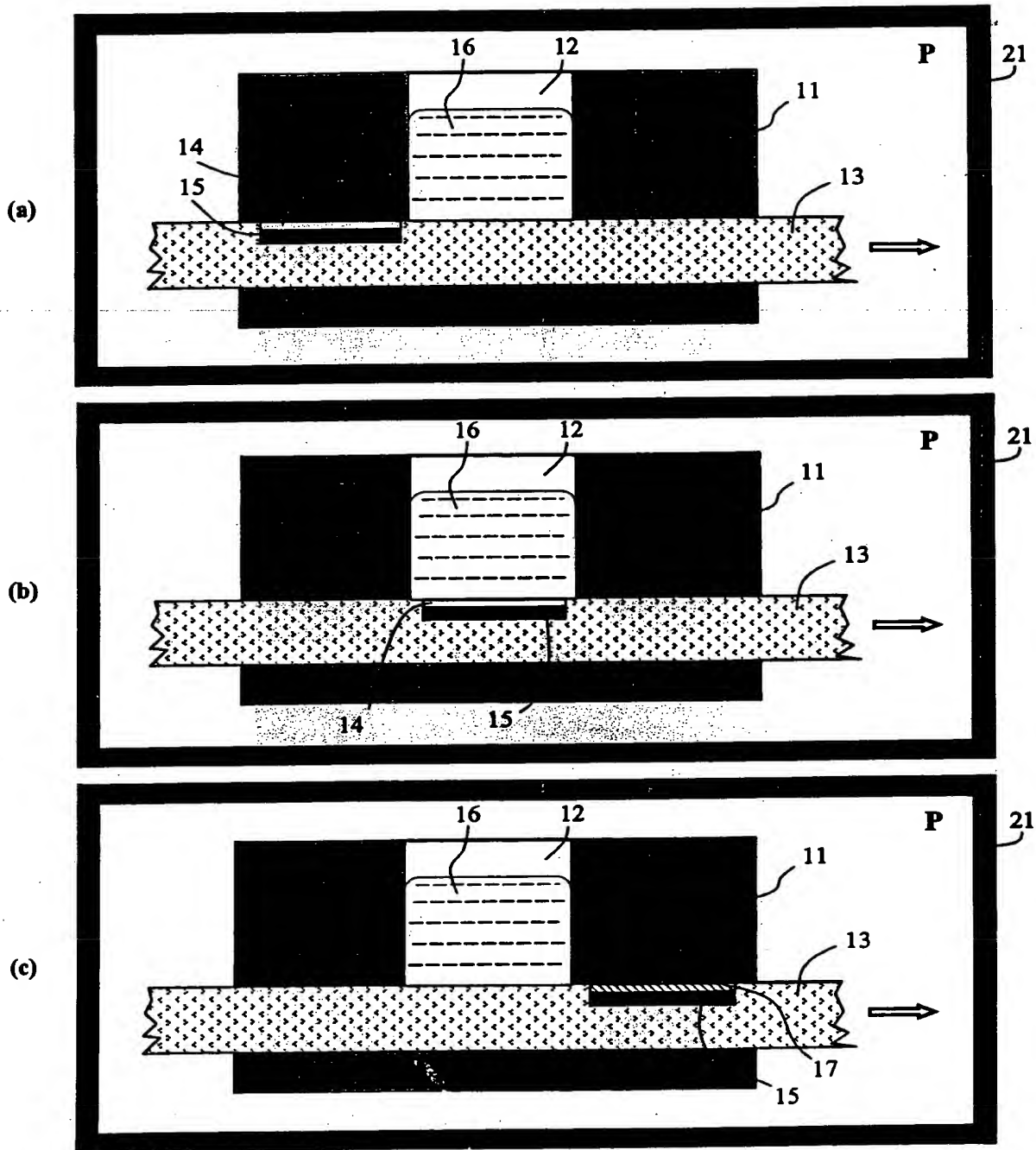
FIGURE 6

Atomic fraction  $x'_{As}$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 7

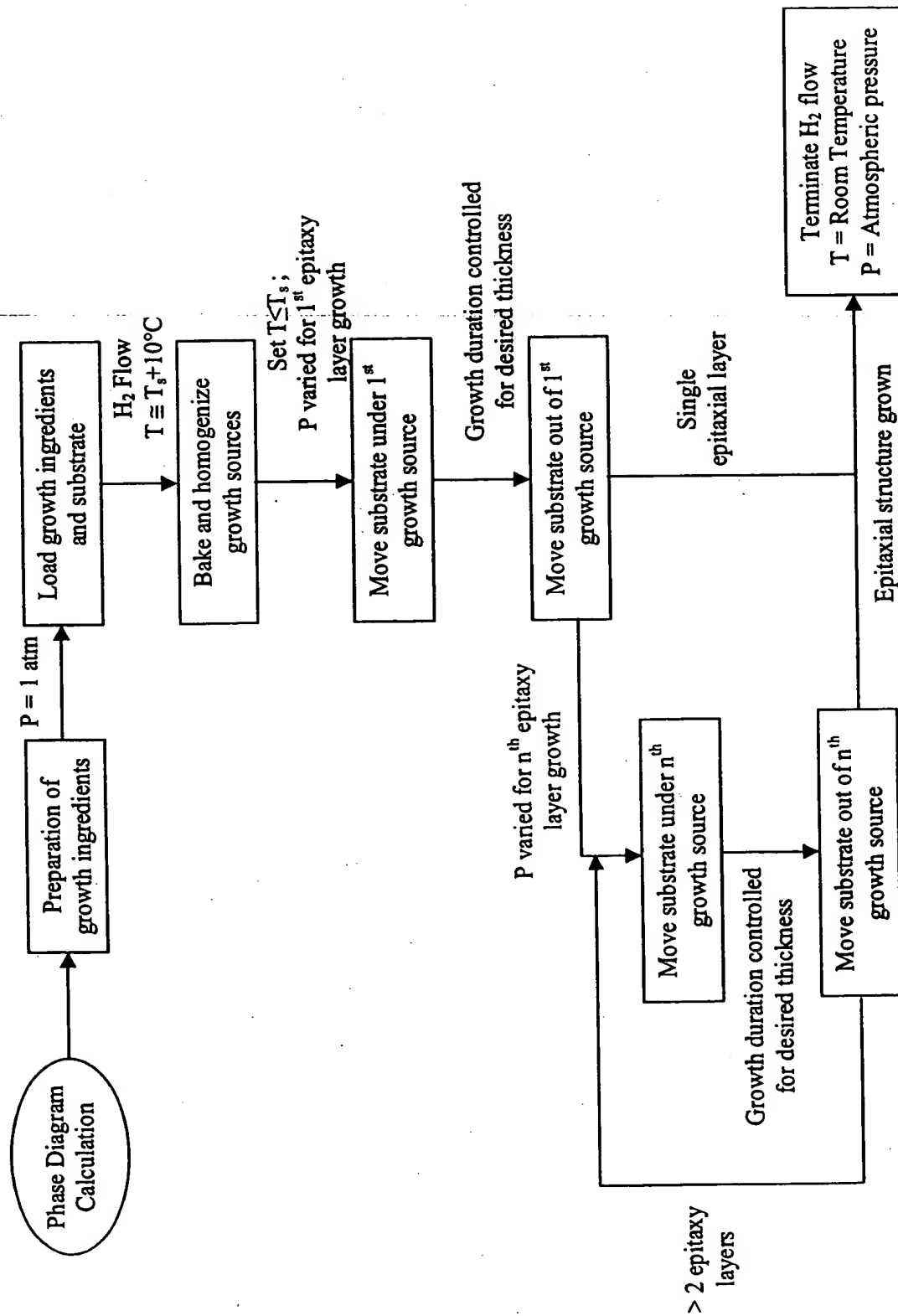
Atomic fraction  $x'_{Sb}$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 8





# Growth of multiple non-compositional-graded layers



**FIGURE 2**  
**Growth of compositional-graded layer**

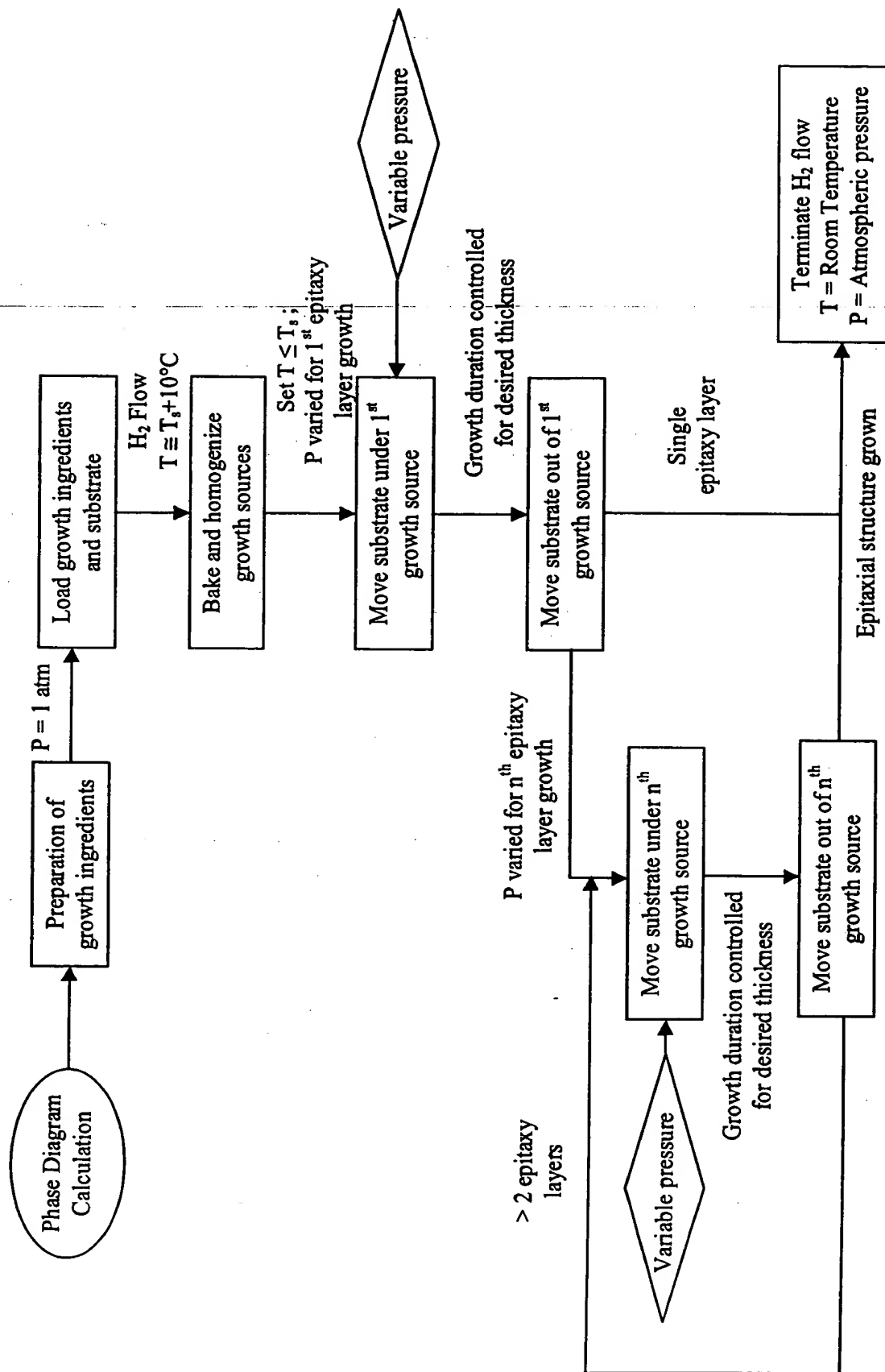
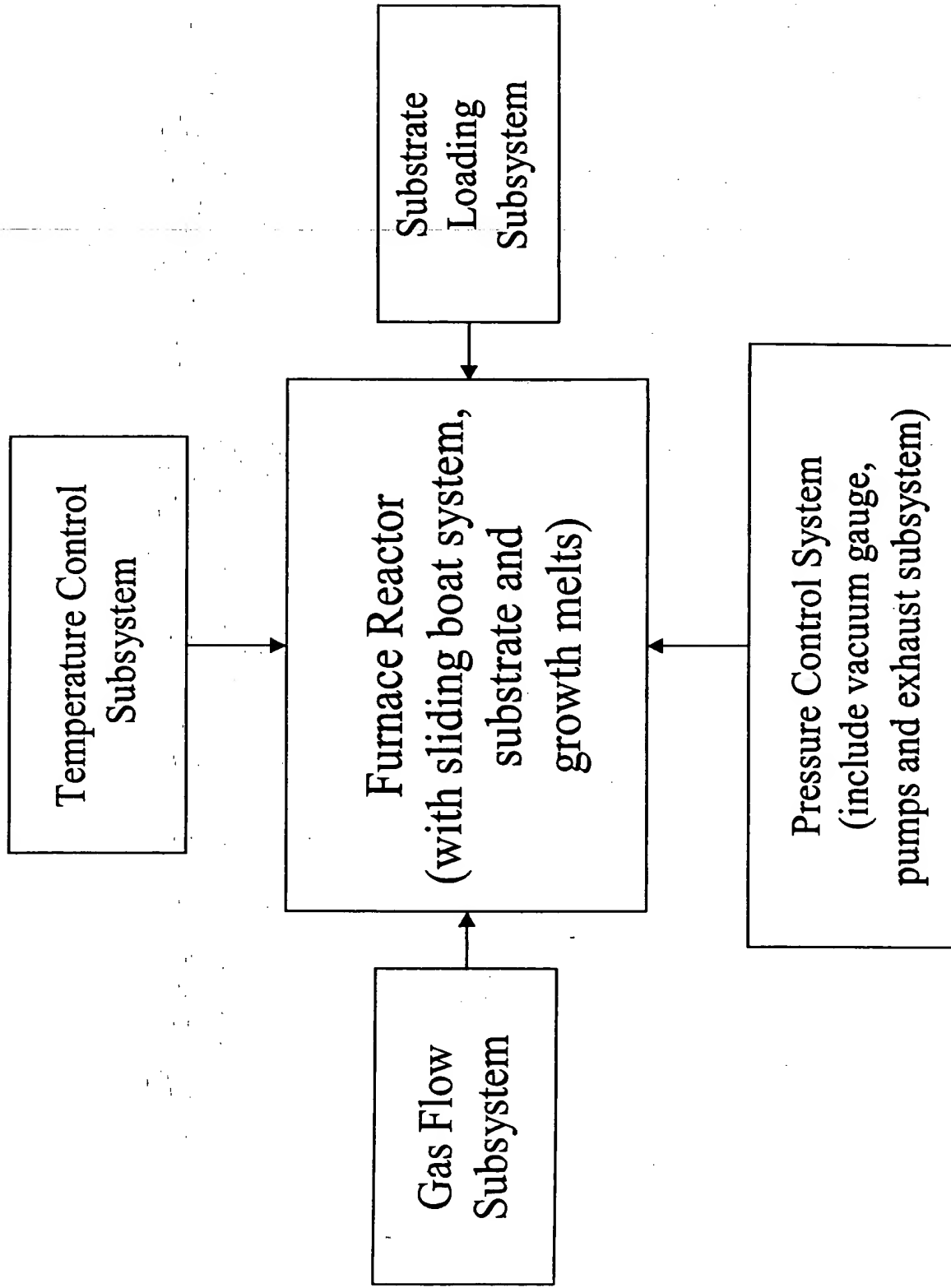
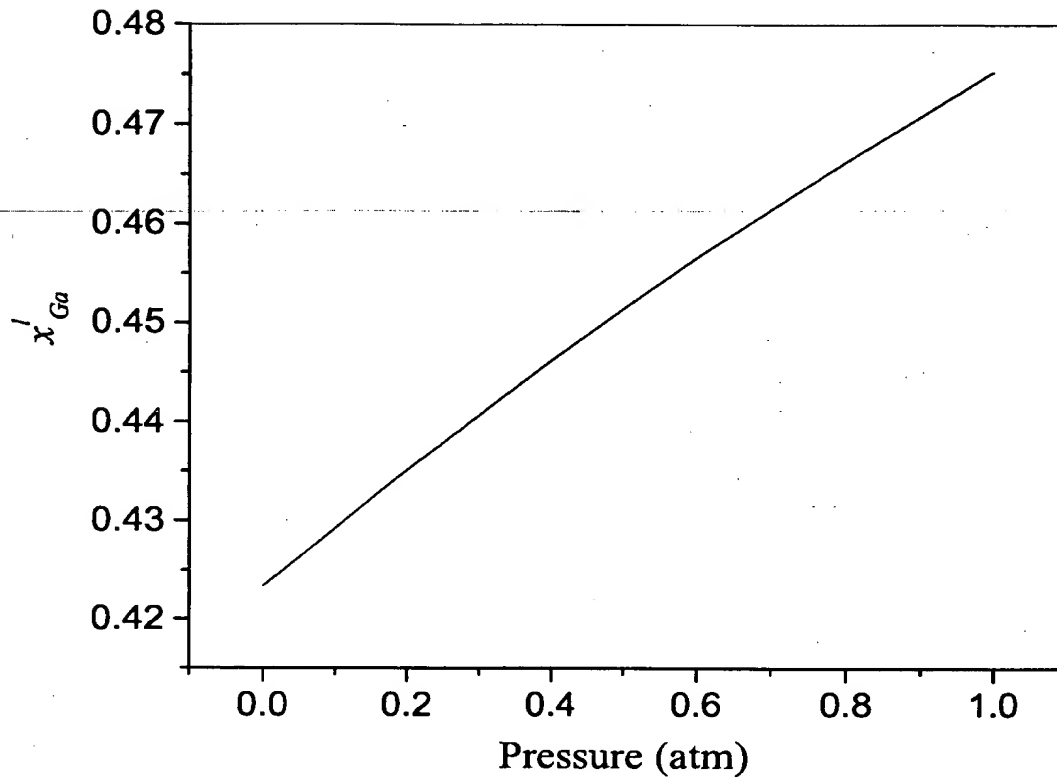


FIGURE 3-13-10

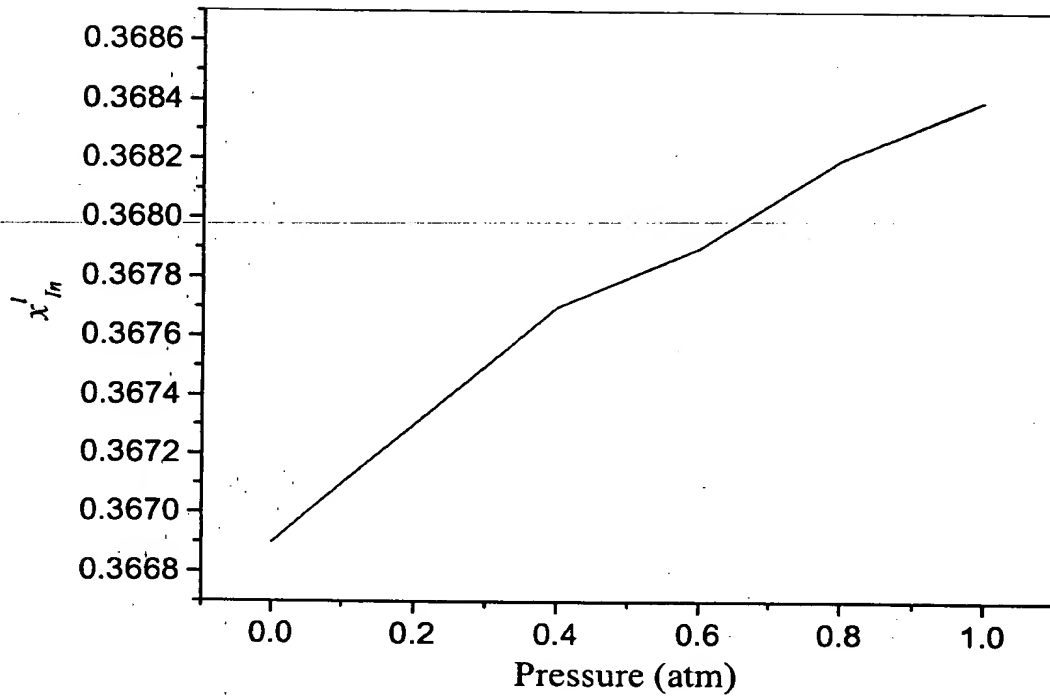


**FIGURE 4**



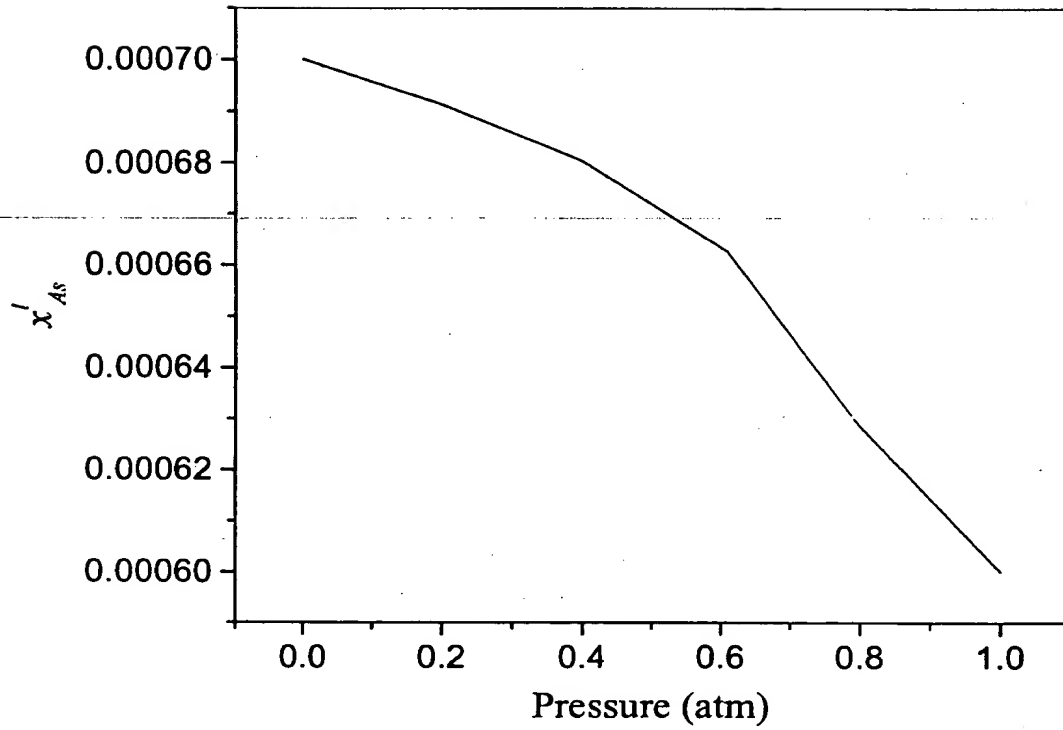
Atomic fraction  $x'_{Ga}$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 5



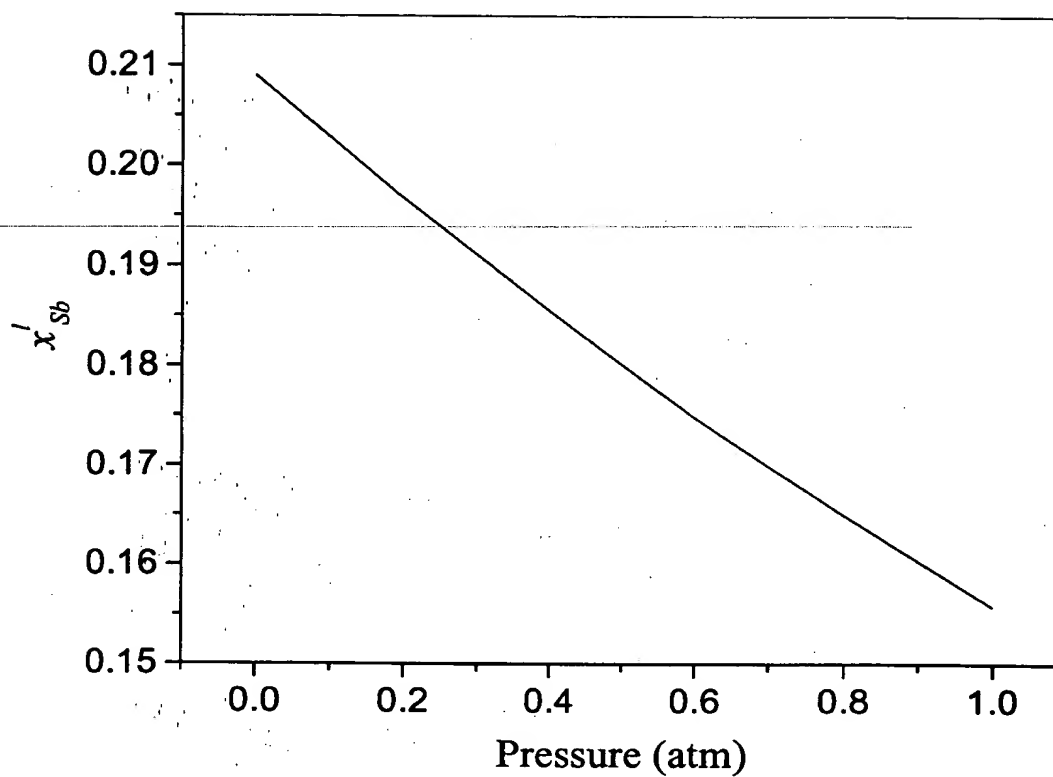
Atomic fraction  $x'_{In}$  in melt for  $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

**FIGURE 6**



Atomic fraction  $x'_{As}$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

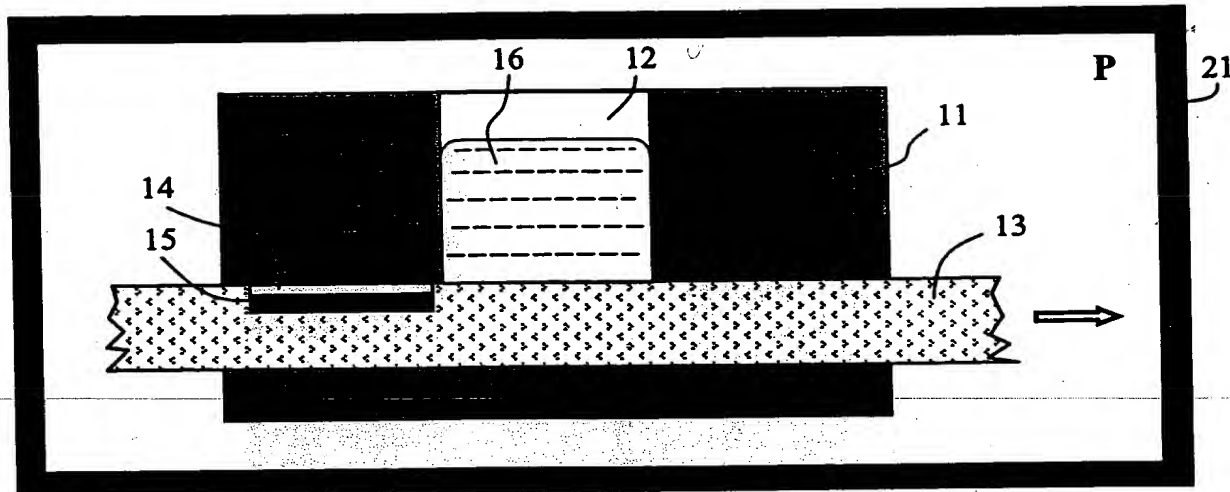
**FIGURE 7**



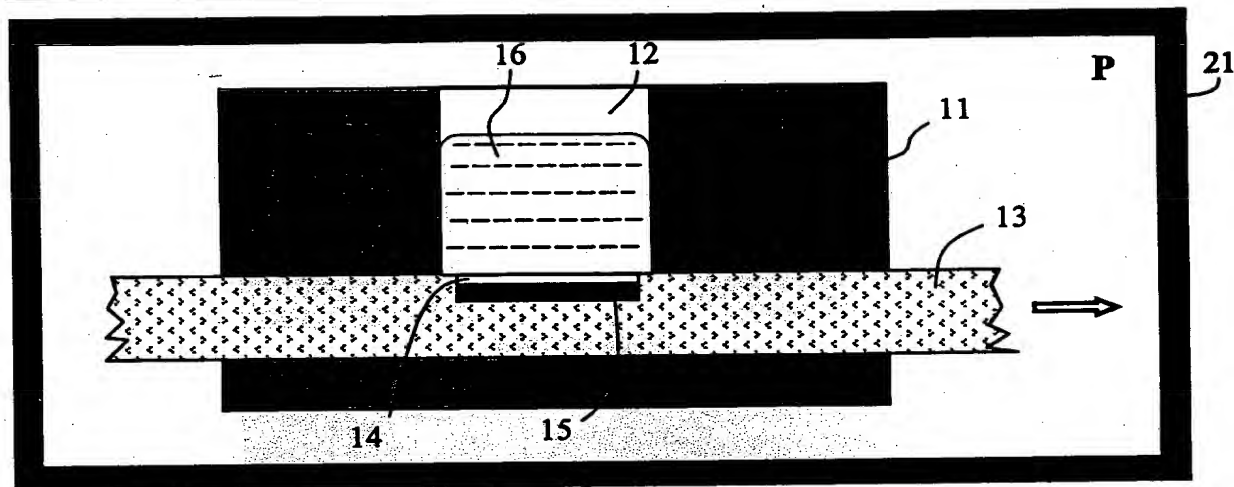
Atomic fraction  $x'_{Sb}$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 8

(a)



(b)



(c)

